

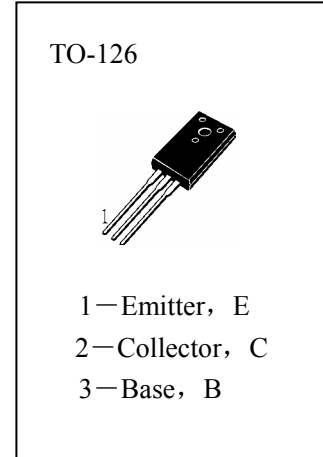
HS600K

APPLICATIONS

Low frequency power amplifier, Medium Seed switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation (T _c =25°C)	1W
V _{CB0}	Collector-Base Voltage	120V
V _{CEO}	Collector-Emitter Voltage	120V
V _{EBO}	Emitter-Base Voltage	5V
I _C	Collector Current	1A

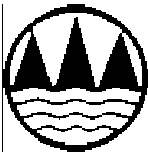


ELECTRICAL CHARACTERISTICS (T_a=25°C)

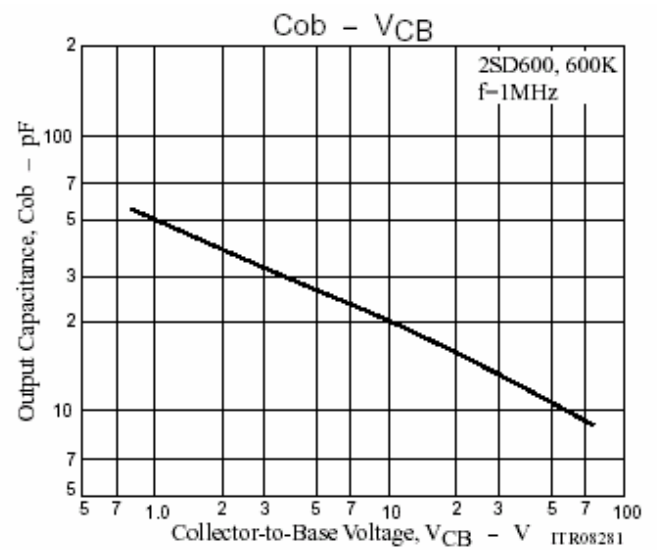
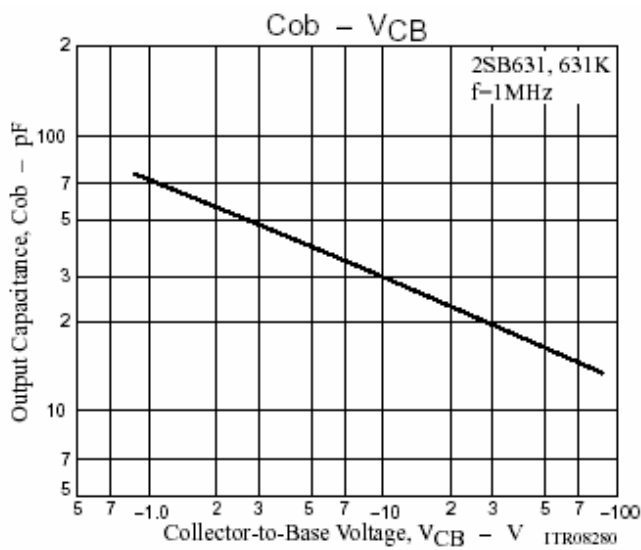
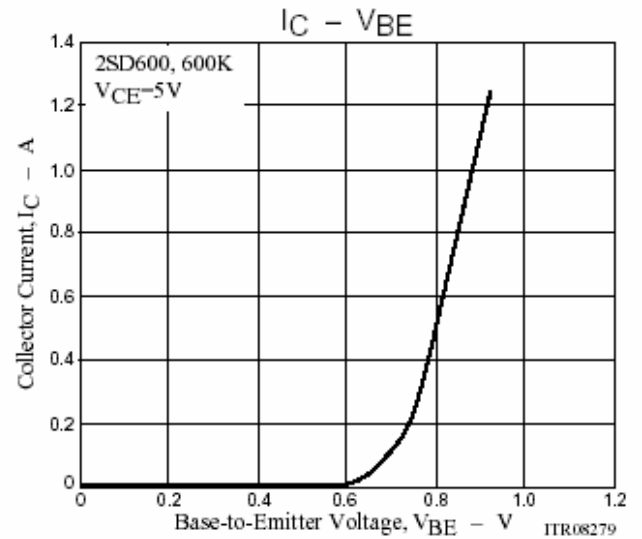
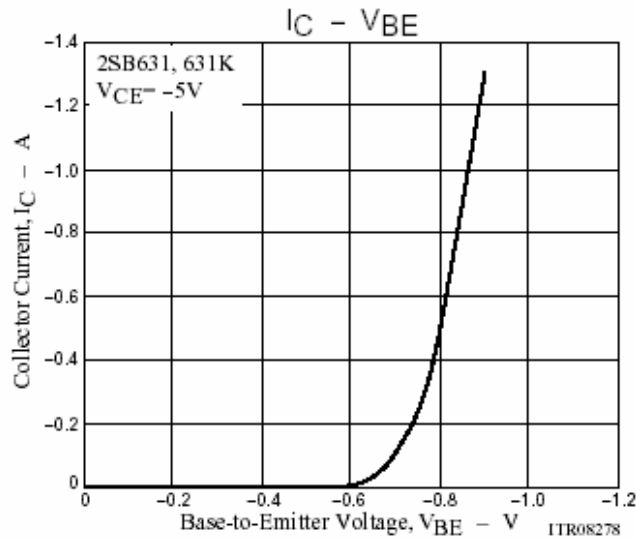
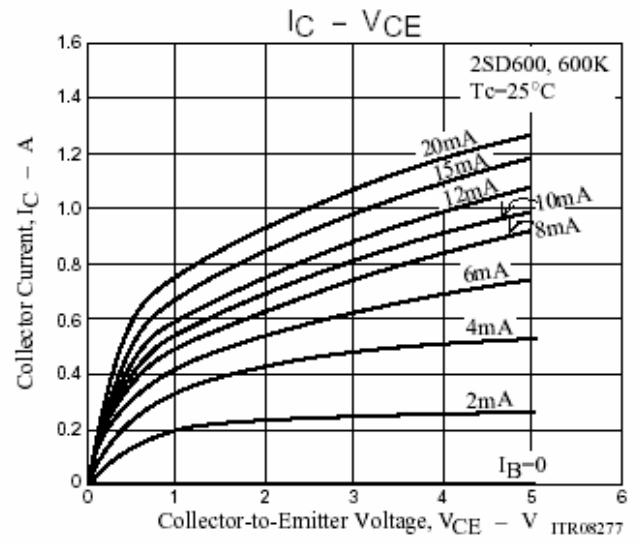
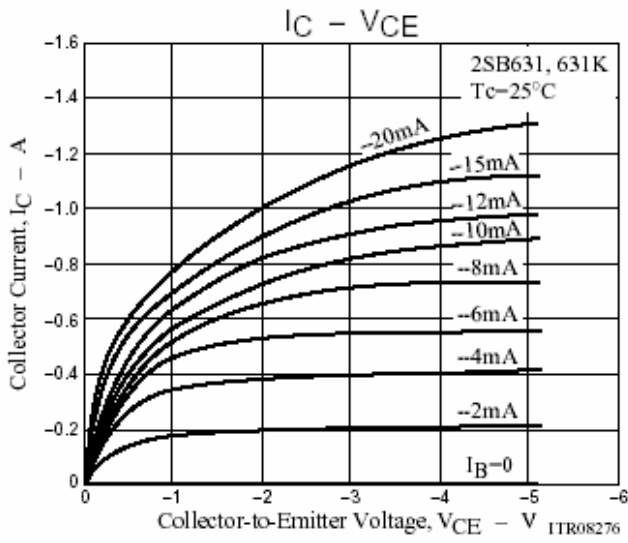
Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	120			V	I _C =10 μA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	120			V	I _C =1mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	5			V	I _E =10 μA, I _C =0
I _{CBO}	Collector Cut-off Current			1	μA	V _{CB} =50V, I _E =0
I _{EBO}	Emitter Cut-off Current			1	μA	V _{EB} =4V, I _C =0
H _{FE} (1)	DC Current Gain	60		320		V _{CE} =5V, I _C =50mA
H _{FE} (2)	DC Current Gain	20				V _{CE} =5V, I _C =500mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage		0.15	0.4	V	I _C =500mA, I _B =50mA
V _{BE(sat)}	Base-Emitter Saturation Voltage		0.85	1.2	V	I _C =500mA, I _B =50mA
t _{OFF}	Turn-Off Time		500		nS	} See specified test circuit
t _{STG}	Storage Time		700		nS	
t _F	Fall Time		100		nS	
f _t	Current Gain-Bandwidth Product		130		MHz	V _{CE} =10V, I _C =50mA,
C _{ob}	Output Capacitance		20		pF	V _{CB} =10V, I _E =0, f=1MHz

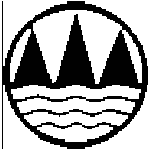
h_{FE} Classification

D	E	F
60—120	100—200	160—320



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